

**ABSTRACT OF THE DISCLOSURE**

Disclosed is a method for crystallizing amorphous silicon, in which a substrate on which an amorphous silicon layer is formed is first prepared, and then a mask is disposed above the substrate. The mask is divided into first and second blocks, the first block having a plurality of first transmission slits and a plurality of interception portions formed between the first transmission slits, the second block having a plurality of second transmission slits alternately arranged with the first transmission slits and a plurality of third transmission slits formed corresponding to middle portions of the first transmission slits. Afterwards, first crystalline regions are formed on the amorphous silicon layer by irradiating a laser beam through the first transmission slits. Finally, non-crystalline regions between the first crystalline regions are crystallized and the nucleation regions are re-crystallized by moving either or both of the substrate and the mask by a predetermined distance and by irradiating a laser beam through the second and third transmission slits.